



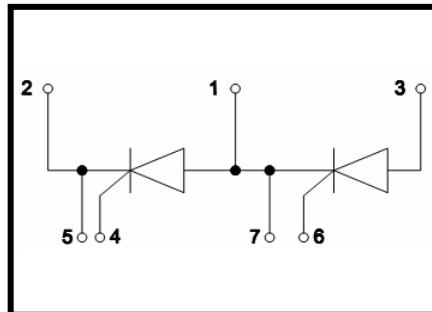
Features

- Isolation voltage 3500 V~
- Industrial Standard Package
- High Surge Capability
- Glass Passivated Chips
- Simple Mounting
- Electrically Isolated by DBC Ceramic



Applications

- DC Motor Control and Drives
- Battery Charges
- Welders
- Power Converters
- Lighting Control
- Heat and Temperature Control



Advantages

- Space and weight savings
- Improved temperature and power cycling

ABSOLUTE MAXIMUM RATINGS

T_C=25°C unless otherwise specified

Symbol	Test Condition	Value	Unit
V _{RRM} /V _{DRM}		1600	V
I _{T(AV)}	T _C =85°C, 180° conduction, half sine wave;	160	A
I _{T(RMS)}	as AC switch;	355	A
I _{TSM}	T _J =45°C, t=10ms (50Hz), sine, V _R =0;	4870	A
	T _J =45°C, t=8.3ms (60Hz), sine, V _R =0;	5100	
	T _J =45°C, t=10ms (50Hz), sine, V _R =V _{RRM} ;	4100	
	T _J =45°C, t=8.3ms (60Hz), sine, V _R =V _{RRM} ;	4300	
I ² t	T _J =45°C, t=10ms (50Hz), sine, V _R =0;	119	KA ² s
	T _J =45°C, t=8.3ms (60Hz), sine, V _R =0;	130	
	T _J =45°C, t=10ms (50Hz), sine, V _R =V _{RRM} ;	84	
	T _J =45°C, t=8.3ms (60Hz), sine, V _R =V _{RRM} ;	92.5	
I _{DRM} /I _{IRRM}	T _J =125°C, V _D =V _R =1600V;	50	mA
dV/dt	T _J =125°C, exponential to 67% rated V _{DRM}	1000	V/us
V _{ISOL}	50Hz, all terminals shorted, t=1s, I _{ISOL} ≤1mA ;	3500	V~
T _J	Max. junction operating temperature range	-40~125	°C
T _{STG}	Max. storage temperature range	-40~150	°C

ELECTRICAL CHARACTERISTICS $T_C=25^\circ C$ unless otherwise specified

Symbol	Test Condition	Min.	Typ.	Max.	Unit
V_{TO}	$16.7\% \times \pi \times I_{AV} < I < \pi \times I_{AV}, T_J = 130^\circ C;$			0.80	V
	$I > \pi \times I_{AV}, T_J = 130^\circ C;$			0.98	V
r_t	$16.7\% \times \pi \times I_{AV} < I < \pi \times I_{AV}, T_J = 130^\circ C;$			1.67	$m\Omega$
	$I > \pi \times I_{AV}, T_J = 130^\circ C;$			1.38	$m\Omega$
I_H	$V_{AK}=6V$, initial $I_T=30A$;			200	mA
I_L	Anode supply =6V, resistive load=1 Ω , gate pulse =10V, 100us;			400	mA
V_{TM}	$I_{TM}=502A, t_d=10\text{ ms, half sine};$		1.54		V
P_{GM}	$t_p \leq 5ms, T_j=125^\circ C;$			12	W
$P_{GM(AV)}$	$f=50Hz, T_j=125^\circ C;$			3	W
I_{GM}	$t_p \leq 5ms, T_j=125^\circ C;$			3	A
$-V_{GT}$				10	V
V_{GT}	$V_A=6V, R_A=1\Omega, T_j=-40^\circ C;$			4	V
	$V_A=6V, R_A=1\Omega;$			2.5	
	$V_A=6V, R_A=1\Omega, T_j=125^\circ C;$			1.7	
I_{GT}	$V_A=6V, R_A=1\Omega, T_j=-40^\circ C;$			270	mA
	$V_A=6V, R_A=1\Omega;$			150	
	$V_A=6V, R_A=1\Omega, T_j=125^\circ C;$			80	
V_{GD}	$V_{AK}=V_{DRM}, T_j=125^\circ C$			0.3	V
I_{GD}				10	mA
di/dt	$I_{TM}=400A$, rated $V_{DRM}, T_j=125^\circ C$			300	A/us

THERMAL AND MECHANICAL CHARACTERISTICS $T_C=25^\circ C$ unless otherwise specified

Symbol	Test Condition	value	Unit
R_{thjc}	DC operation, per junction;	0.18	K/W
R_{THCS}	Mounting surface smooth, flat and greased, per junction;	0.1	K/W
M_d	Mounting torque(M6)	4 to 6	$N\cdot m$
	Terminal connection torque(M6)		
Weight	Typical value	156	g

Characteristic curves

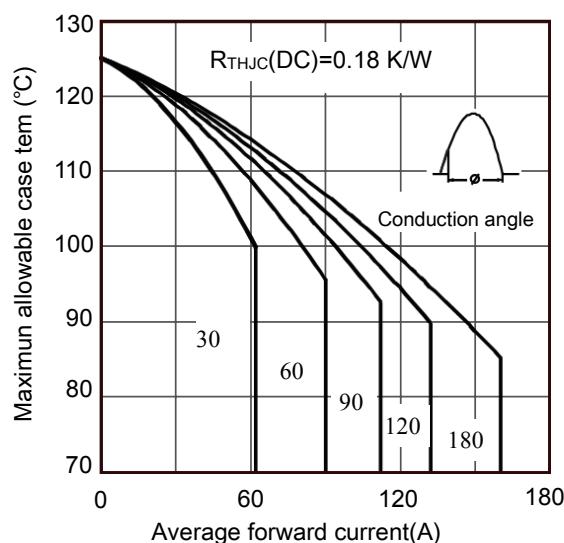


Figure 1. current rating characteristics

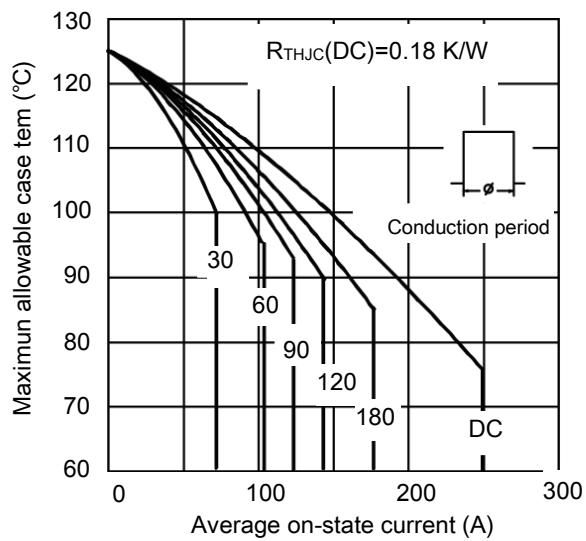


Figure 2. current rating characteristics

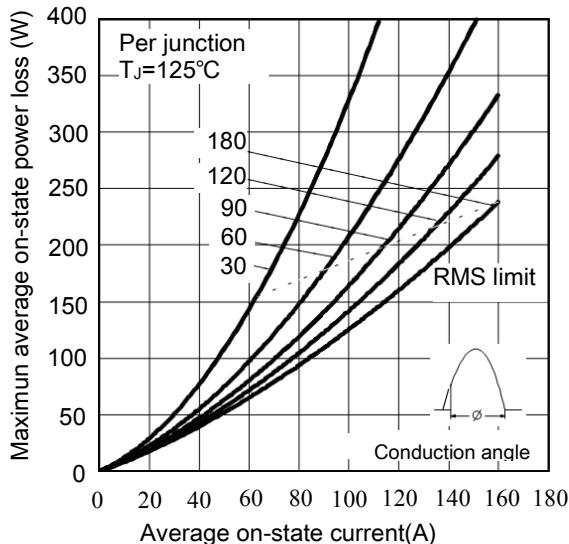


Figure 3. on-state power loss characteristics

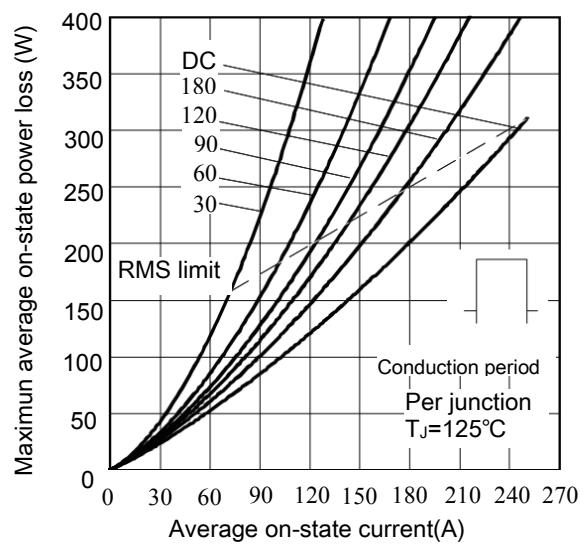


Figure 4. on-state power loss characteristics

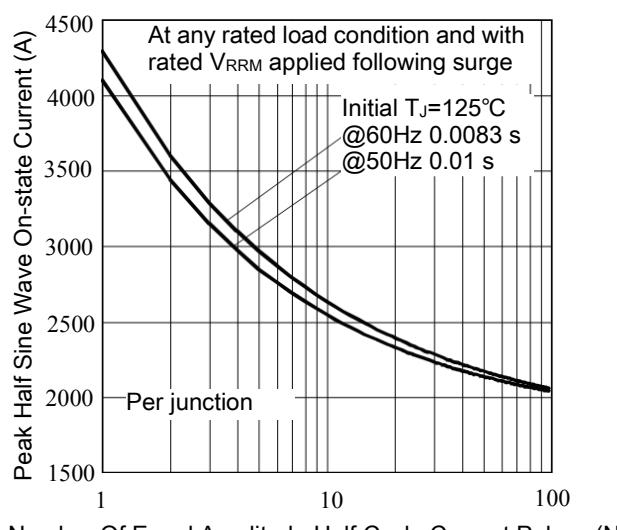


Figure 5. Maximum Non-Repetitive Surge Current

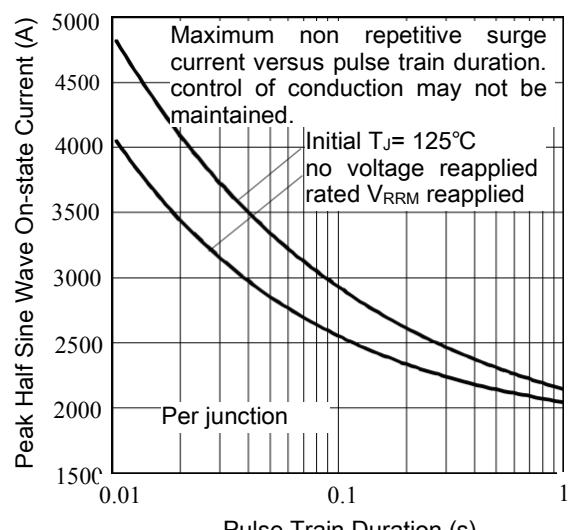


Figure 6. Maximum Non-Repetitive Surge Current

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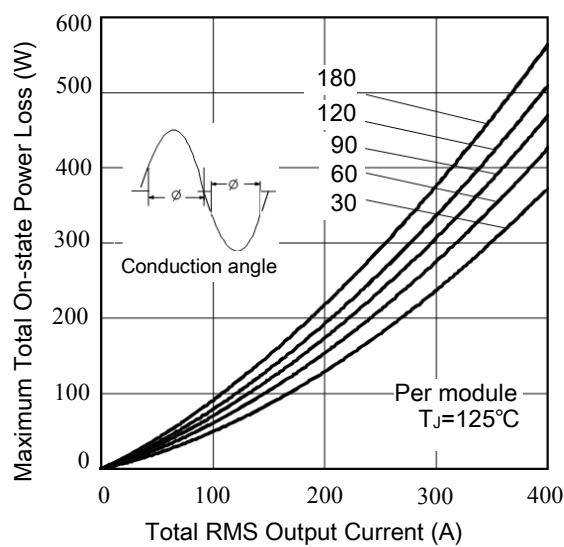


Figure 7. On-State Power Loss Characteristics-1

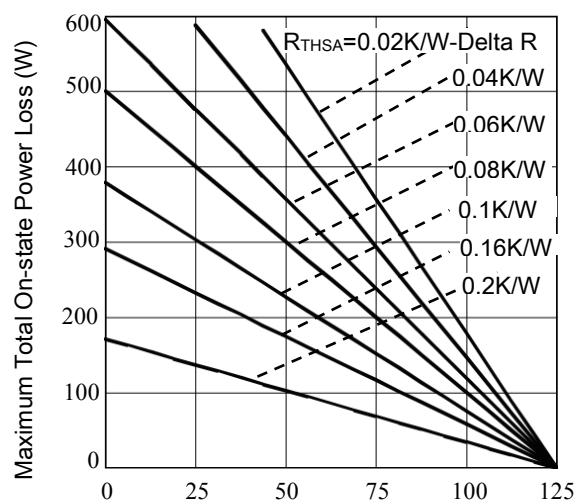


Figure 8 On-State Power Loss Characteristics-2

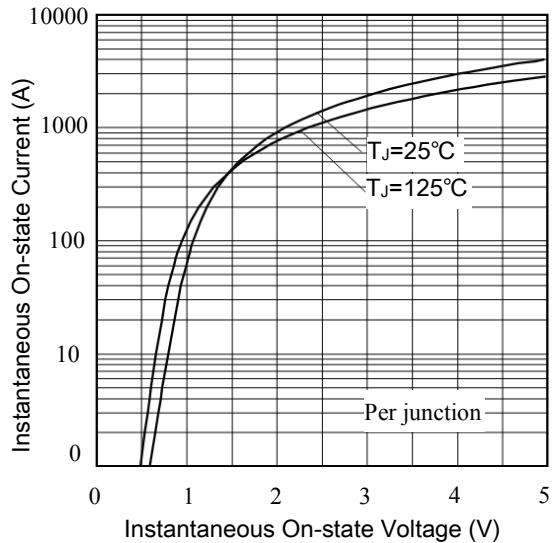


Figure 9 On State Voltage Drop Characteristics

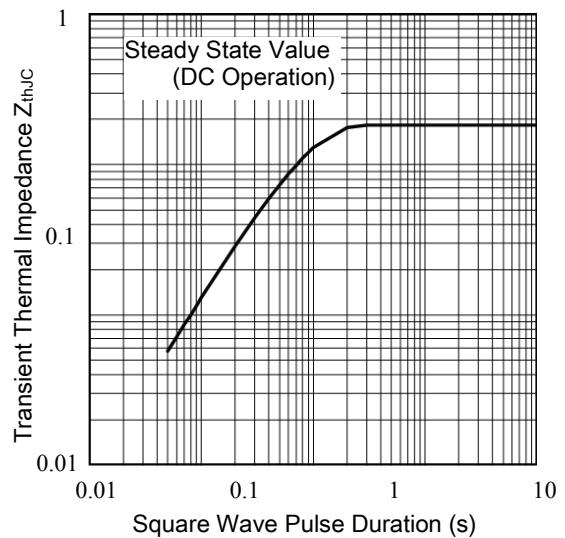


Figure 10 Thermal Impedance Z_{thJC} Characteristics

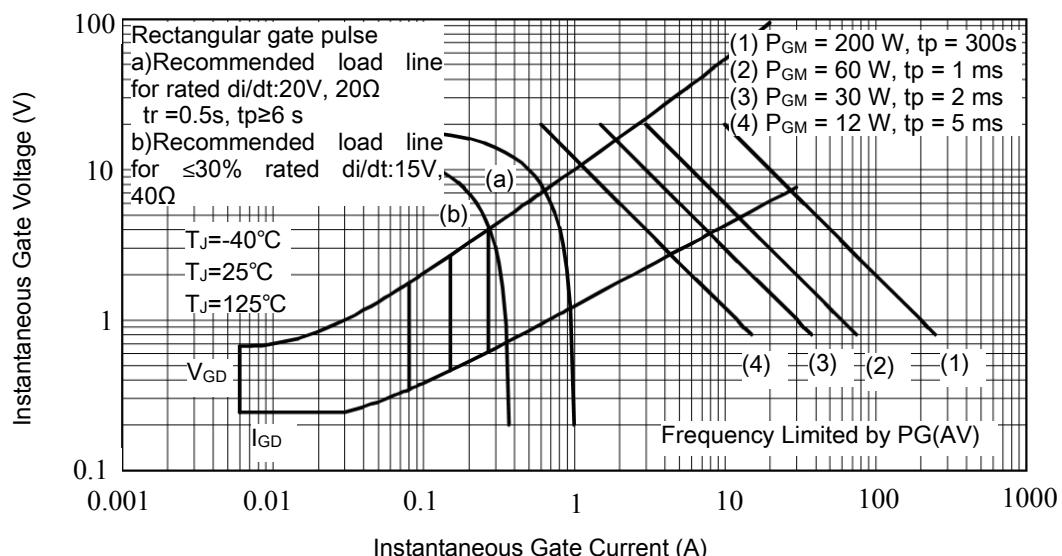


Figure 11 Gate Characteristics

Package Outline (Dimensions in mm)

